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				Application Number	Not Yet Assigned 10/616,721
				Filing Date	Concurrently Herewith 7/10/03
				First Named Inventor	Won-Ho Lee
				Art Unit	NA 2878
				Examiner Name	Not Yet Assigned Le
Sheet	1	of	1	Attorney Docket Number	29926/39500

U.S. PATENT DOCUMENTS					
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			²
	C1	Fujieda et al., "Dependence of Si PH Junction Perimeter Leakage on the Channel-Stop Boron Dose and Interlayer Material," <i>IEEE Electron Device Letters</i> , Vol. 20, No. 8, 418-420 (August 1999).			
	C2	Morris et al., "An Accurate and Efficient Model for Boron Implants through Thin Oxide Layers into Single-Crystal Silicon," <i>IEEE Transactions on Semiconductor Manufacturing</i> 8(4) 408-413 (November 1995).			
	C3	Son et al., "Blanket Tilt Implanted Shallow Trench Isolation (BTI0STI) Process for Enhanced Dram Retention Time Characteristics," <i>IEEE</i> 122-124 (1999).			
	C4	Walther et al., "Dopant Channeling as a Function of Implant Angle for Low Energy Applications," <i>IEEE</i> 126-129 (1999).			

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